



ZHEJIANG UNIÜ-NE Technology CO., LTD

浙江宇力微新能源科技有限公司



U3116C Data Sheet

V 1.3

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Half-bridge of power MOSFET/IGBT Drive

General Description

The U3116C Fully operated to +350V is high voltage, high speed power MOSFET and IGBT driver with dependent high and low side referenced output channels.

The logic input is compatible with standard CMOS or LSTTL output, down to 3.3V logic. The output drivers feature a high pulse current buffer stage designed for minimum driver cross-conduction. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high side configuration which operates up to 350 volts.

Product Summary

V _{OFFSET}	350V
I _{O+/-}	1.0A / 1.2A
V _{CCon/off(typ.)}	8.7V & 8.3V
ton/off (typ.)	450 & 150ns
Deadtime (typ.)	300 ns
Work Tem	-40 ~150 °C

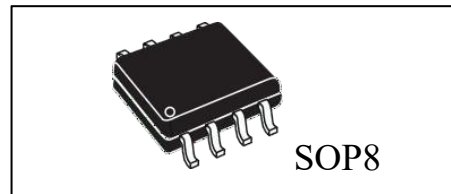
Key Features

- Integrated bootstrap Diode⁽¹⁾
- Floating channel designed for bootstrap operation
- Fully operational to +350V
- Tolerant to negative transient voltage dV/dt immune
- Gate drive supply range from 9 to 20V
- Undervoltage lockout
- 3.3V, 5V and 15V input logic compatible
- Cross-conduction prevention logic
- Matched propagation delay for both channels

Applications

- Home appliances
- Industrial applications and drives
- Motor drivers
- DC- AC Converter, PMDC and PMAC motors
- Induction heating
- HVAC

Packages

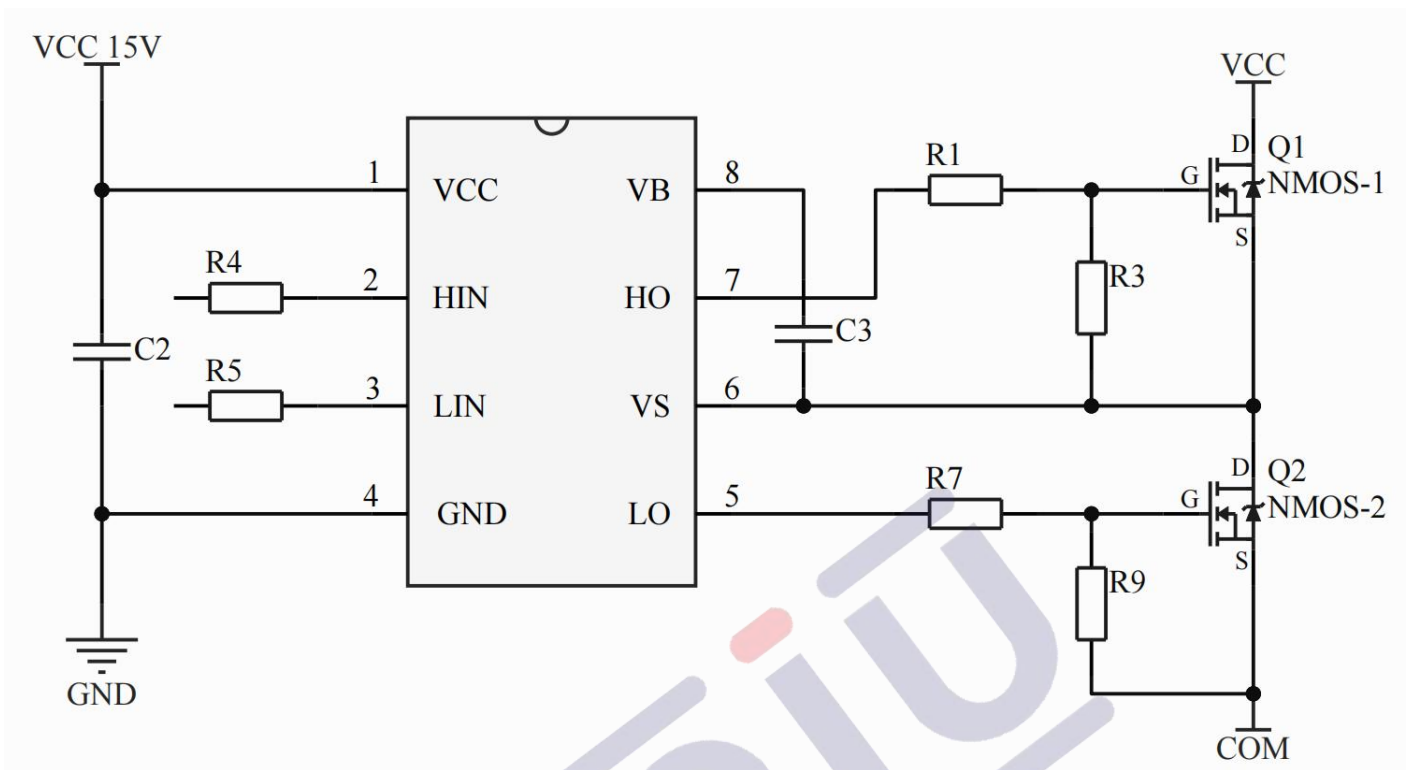


Product information

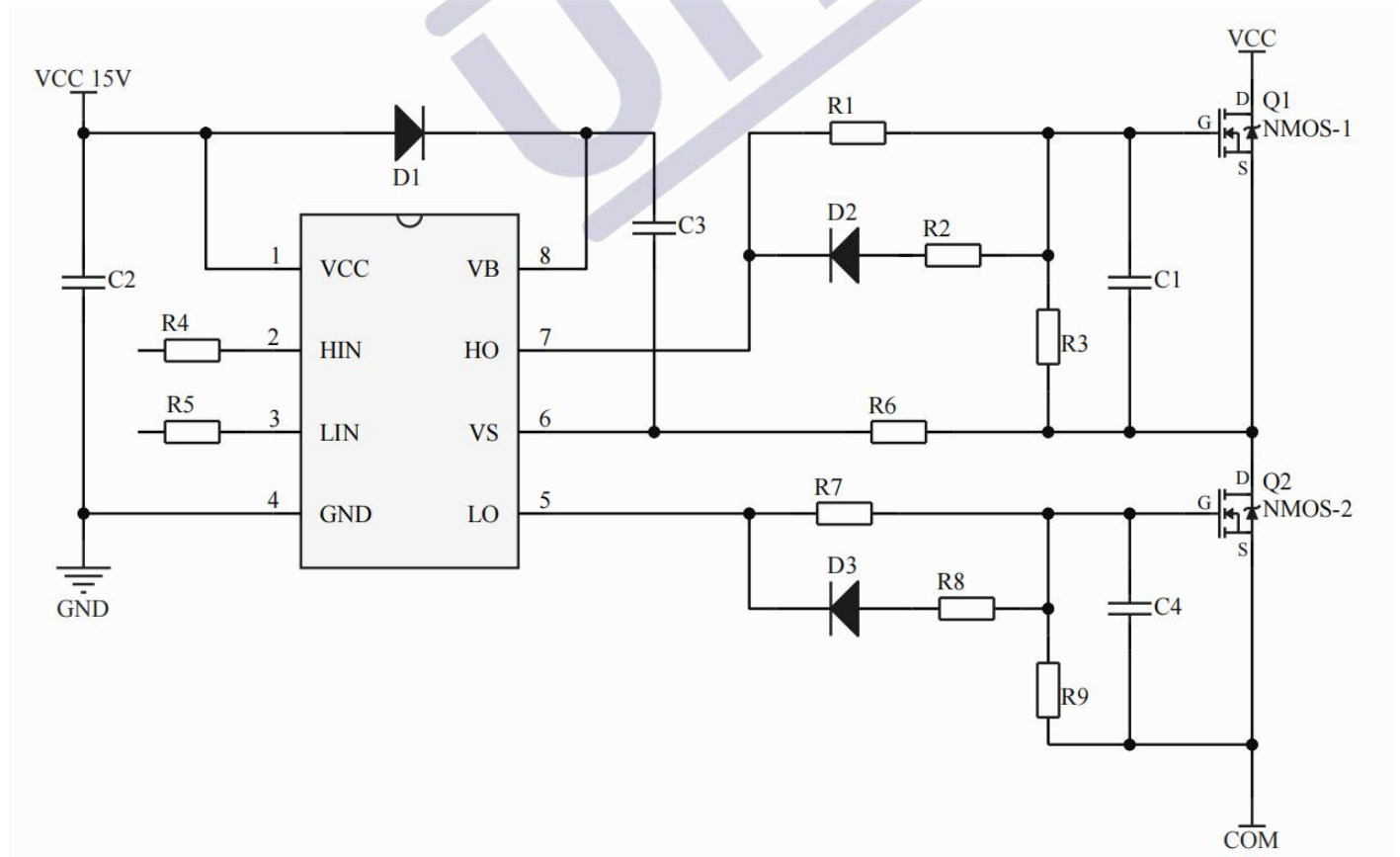
Base Part Number	Package Type	Standard OUT		V _{OFFSET}	Logic Control
		IO+	IO-		
U3116C	SOP8	1.0A	1.2A	350V	HIN & LIN

Note: (1) When using internal diode bootstrap power supply, please match the capacitor and MOS, and fully test and verify

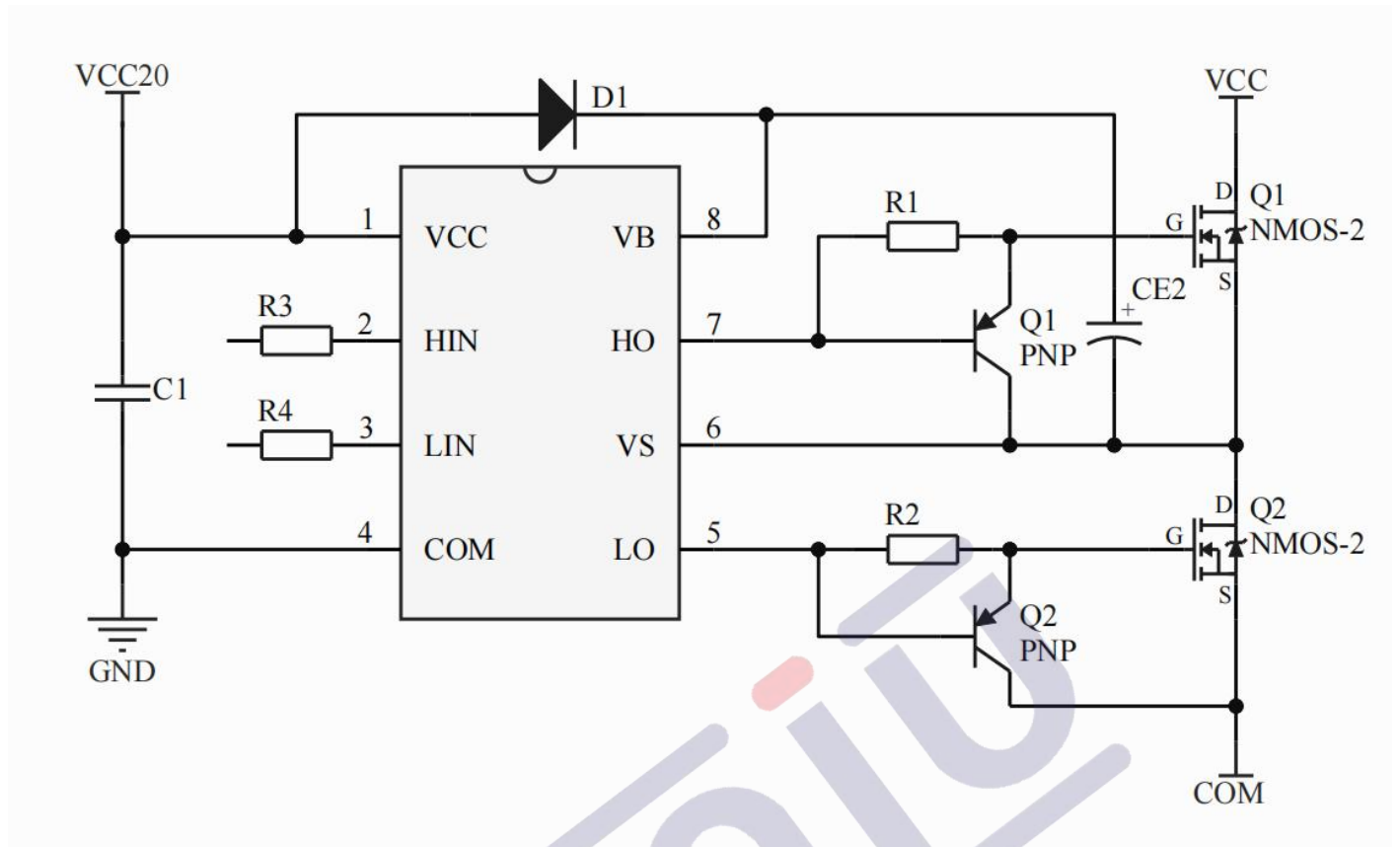
Typical Connection



Small power application



Typical application



Much Big POWER application

Note: The above circuits and parameters are for reference only. The actual application circuit should be designed with the measured results in setting the parameters

1、版本记录

DATE	REV.	DESCRIPTION
2020/04/19	1.0	首次发布
2023/07/10	1.1	优化延时、边沿时间及欠压保护
2023/10/25	1.2	增加内置二极管应用
2024/02/27	1.3	拆分U3115C和U3116C规格书

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